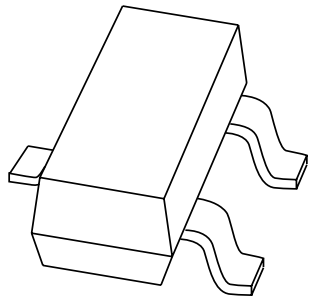


DATA SHEET



BCF32; BCF33 NPN general purpose transistors

Product specification
Supersedes data of September 1994
File under Discrete Semiconductors, SC04

1997 May 20

NPN general purpose transistors

BCF32; BCF33

FEATURES

- Low current (max. 100 mA)
- Low voltage (max. 32 V).

APPLICATIONS

- Low level, low noise general purpose applications in thick and thin-film circuits.

DESCRIPTION

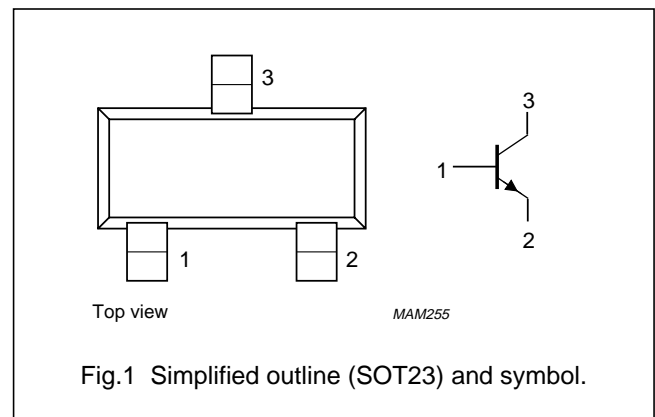
NPN transistor in a SOT23 plastic package.
PNP complements: BCF29 and BCF30.

MARKING

| TYPE NUMBER | MARKING CODE |
|-------------|--------------|
| BCF32 | D7p |
| BCF33 | D8p |

PINNING

| PIN | DESCRIPTION |
|-----|-------------|
| 1 | base |
| 2 | emitter |
| 3 | collector |



QUICK REFERENCE DATA

| SYMBOL | PARAMETER | CONDITIONS | MIN. | MAX. | UNIT |
|-----------|---------------------------|---------------------------------------------------------------|------|------|------|
| V_{CBO} | collector-base voltage | open emitter | – | 32 | V |
| V_{CEO} | collector-emitter voltage | open base | – | 32 | V |
| I_{CM} | peak collector current | | – | 200 | mA |
| P_{tot} | total power dissipation | $T_{amb} \leq 25\text{ °C}$ | – | 250 | mW |
| h_{FE} | DC current gain | $I_C = 2\text{ mA}; V_{CE} = 5\text{ V}$ | | | |
| | BCF32 | | 200 | 450 | |
| | BCF33 | | 420 | 800 | |
| f_T | transition frequency | $I_C = 10\text{ mA}; V_{CE} = 5\text{ V}; f = 100\text{ MHz}$ | 100 | – | MHz |

NPN general purpose transistors

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LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 134).

| SYMBOL | PARAMETER | CONDITIONS | MIN. | MAX. | UNIT |
|------------------|-------------------------------|----------------------------------|------|------|------|
| V _{CBO} | collector-base voltage | open emitter | – | 32 | V |
| V _{CEO} | collector-emitter voltage | open base | – | 32 | V |
| V _{EBO} | emitter-base voltage | open collector | – | 5 | V |
| I _C | collector current (DC) | | – | 100 | mA |
| I _{CM} | peak collector current | | – | 200 | mA |
| I _{BM} | peak base current | | – | 100 | mA |
| P _{tot} | total power dissipation | T _{amb} ≤ 25 °C; note 1 | – | 250 | mW |
| T _{stg} | storage temperature | | –65 | +150 | °C |
| T _j | junction temperature | | – | 150 | °C |
| T _{amb} | operating ambient temperature | | –65 | +150 | °C |

Note

1. Transistor mounted on an FR4 printed-circuit board.

THERMAL CHARACTERISTICS

| SYMBOL | PARAMETER | CONDITIONS | VALUE | UNIT |
|---------------------|---------------------------------------------|------------|-------|------|
| R _{th j-a} | thermal resistance from junction to ambient | note 1 | 500 | K/W |

Note

1. Transistor mounted on an FR4 printed-circuit board.

NPN general purpose transistors

BCF32; BCF33

CHARACTERISTICS

$T_j = 25\text{ °C}$ unless otherwise specified.

| SYMBOL | PARAMETER | CONDITIONS | MIN. | TYP. | MAX. | UNIT |
|-------------|--------------------------------------|-----------------------------------------------------------------------------------------------------------------------|------|------|------|---------------|
| I_{CBO} | collector cut-off current | $I_E = 0; V_{CB} = 32\text{ V}$ | – | – | 100 | nA |
| | | $I_E = 0; V_{CB} = 32\text{ V}; T_j = 100\text{ °C}$ | – | – | 10 | μA |
| I_{EBO} | emitter cut-off current | $I_C = 0; V_{EB} = 5\text{ V}$ | – | – | 100 | nA |
| h_{FE} | DC current gain BCF32 BCF33 | $I_C = 10\text{ }\mu\text{A}; V_{CE} = 5\text{ V}$ | – | 150 | – | |
| | | | – | 270 | – | |
| h_{FE} | DC current gain BCF32 BCF33 | $I_C = 2\text{ mA}; V_{CE} = 5\text{ V}$ | 200 | – | 450 | |
| | | | 420 | – | 800 | |
| V_{CEsat} | collector-emitter saturation voltage | $I_C = 10\text{ mA}; I_B = 0.5\text{ mA}$ | – | 120 | 250 | mV |
| | | $I_C = 50\text{ mA}; I_B = 2.5\text{ mA}$ | – | 210 | – | mV |
| V_{BEsat} | base-emitter saturation voltage | $I_C = 10\text{ mA}; I_B = 0.5\text{ mA}$ | – | 750 | – | mV |
| | | $I_C = 50\text{ mA}; I_B = 2.5\text{ mA}$ | – | 850 | – | mV |
| V_{BE} | base-emitter voltage | $I_C = 2\text{ mA}; V_{CE} = 5\text{ V}$ | 550 | – | 700 | mV |
| C_c | collector capacitance | $I_E = i_e = 0; V_{CB} = 10\text{ V}; f = 1\text{ MHz}$ | – | 2.5 | – | pF |
| f_T | transition frequency | $I_C = 10\text{ mA}; V_{CE} = 5\text{ V}; f = 100\text{ MHz}$ | 100 | – | – | MHz |
| F | noise figure | $I_C = 200\text{ }\mu\text{A}; V_{CE} = 5\text{ V}; R_S = 2\text{ k}\Omega;$ $f = 1\text{ kHz}; B = 200\text{ Hz}$ | – | 1.2 | 4 | dB |

NPN general purpose transistors

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PACKAGE OUTLINE

Plastic surface mounted package; 3 leads

SOT23



NPN general purpose transistors

BCF32; BCF33

DEFINITIONS

| | |
|-----------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------|---------------------------------------------------------------------------------------|
| Data Sheet Status | |
| Objective specification | This data sheet contains target or goal specifications for product development. |
| Preliminary specification | This data sheet contains preliminary data; supplementary data may be published later. |
| Product specification | This data sheet contains final product specifications. |
| Limiting values | |
| Limiting values given are in accordance with the Absolute Maximum Rating System (IEC 134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of the specification is not implied. Exposure to limiting values for extended periods may affect device reliability. | |
| Application information | |
| Where application information is given, it is advisory and does not form part of the specification. | |

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NPN general purpose transistors

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